

# **PBHV9115X**

150 V, 1 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor
Rev. 01 — 10 March 2010 Product data

Product data sheet

#### 1. **Product profile**

### 1.1 General description

PNP high-voltage low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a SOT89 (SC-62/TO-243) small and flat Surface-Mounted Device (SMD) plastic package.

#### 1.2 Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>

### 1.3 Applications

- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-150	V
I <sub>C</sub>	collector current		-	-	-1	А
h <sub>FE</sub>	DC current gain	$V_{CE} = -10 \text{ V};$ $I_{C} = -50 \text{ mA}$	100	220	-	

#### **Pinning information** 2.

Table 2. **Pinning** 

Pin	Description	Simplified outline	Graphic symbol
1	emitter		_
2	collector		2 J
3	base	3 2 1	3 — 1 sym079



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# 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBHV9115X	SC-62	plastic surface-mounted package; collector pad for good heat transfer; 3 leads	SOT89			

## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PBHV9115X	*4G

<sup>[1] \* = -:</sup> made in Hong Kong

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	-200	V
$V_{CEO}$	collector-emitter voltage	open base	-	-150	V
V <sub>CESM</sub>	collector-emitter peak voltage	$V_{BE} = 0 V$	-	-200	V
$V_{EBO}$	emitter-base voltage	open collector	-	-6	V
I <sub>C</sub>	collector current		-	-1	Α
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-2	Α
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	-400	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	<u>[1]</u>	520	mW
			[2]	1.5	W
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
$T_{stg}$	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

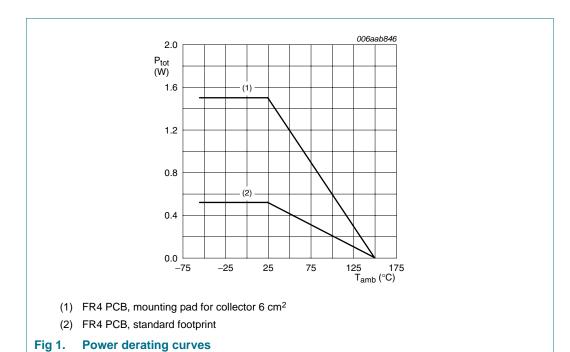
<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

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### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		<u>[1]</u> -	-	240	K/W
			[2] _	-	80	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	20	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

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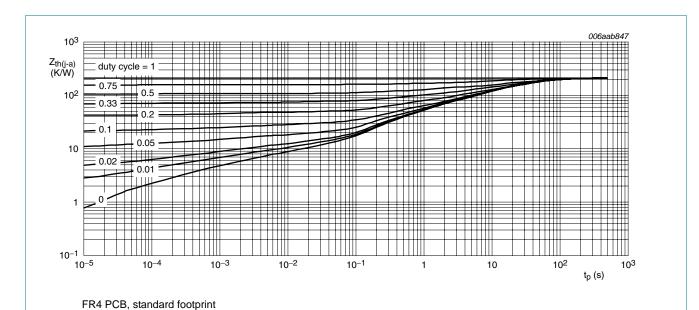
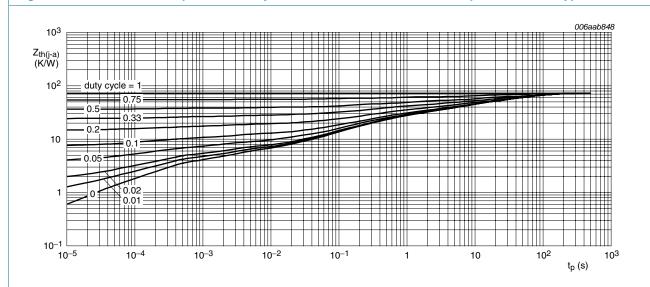


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 7. Characteristics

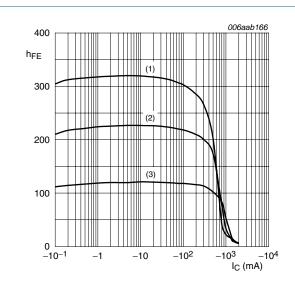
**Table 7. Characteristics** 

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -120 \text{ V};$ $I_E = 0 \text{ A}$		-	-	-100	nA
		$V_{CB} = -120 \text{ V};$ $I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$		-	-	-10	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = -120 \text{ V};$ $V_{BE} = 0 \text{ V}$		-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -4 \text{ V}; I_C = 0 \text{ A}$		-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -10 \text{ V}$					
		$I_C = -50 \text{ mA}$		100	220	-	
		$I_{\rm C} = -100 \; {\rm mA}$	[1]	100	220	-	
		I <sub>C</sub> = -1 A	[1]	10	30	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -100 \text{ mA};$ $I_B = -10 \text{ mA}$	[1]	-	-60	-120	mV
		$I_C = -100 \text{ mA};$ $I_B = -20 \text{ mA}$	<u>[1]</u>	-	-50	-100	mV
		$I_C = -500 \text{ mA};$ $I_B = -50 \text{ mA}$	<u>[1]</u>	-	-200	-300	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -1 A;$ $I_B = -100 \text{ mA}$	[1]	-	-1	-1.2	V
t <sub>d</sub>	delay time	$V_{CC} = -6 \text{ V};$		-	8	-	ns
t <sub>r</sub>	rise time	$I_{\rm C} = -0.5  \text{A};$		-	282	-	ns
t <sub>on</sub>	turn-on time	$-I_{Bon} = -0.1 \text{ A};$ $I_{Boff} = 0.1 \text{ A}$		-	290	-	ns
ts	storage time			-	430	-	ns
t <sub>f</sub>	fall time			-	300	-	ns
t <sub>off</sub>	turn-off time			-	730	-	ns
f <sub>T</sub>	transition frequency	$V_{CE} = -10 \text{ V};$ $I_{C} = -10 \text{ mA};$ $f = 100 \text{ MHz}$		-	115	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -20 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$		-	10	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = -0.5 \text{ V};$ $I_{C} = i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}$		-	150	-	pF

<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

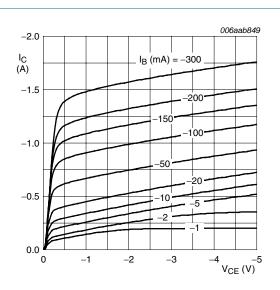
### 150 V, 1 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor



$$V_{CE} = -10 \text{ V}$$

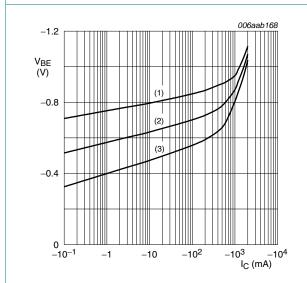
- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -55 \, ^{\circ}C$

Fig 4. DC current gain as a function of collector current; typical values



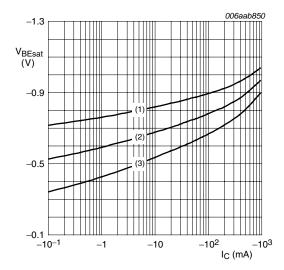
 $T_{amb} = 25 \, ^{\circ}C$ 

Fig 5. Collector current as a function of collector-emitter voltage; typical values



- $V_{CE} = -10 \text{ V}$
- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3) T<sub>amb</sub> = 100 °C

Fig 6. Base-emitter voltage as a function of collector current; typical values

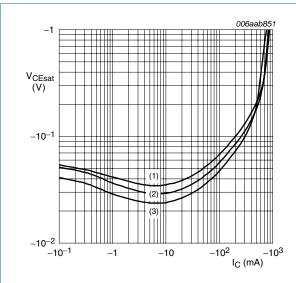


 $I_{\rm C}/I_{\rm B}=10$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 7. Base-emitter saturation voltage as a function of collector current; typical values

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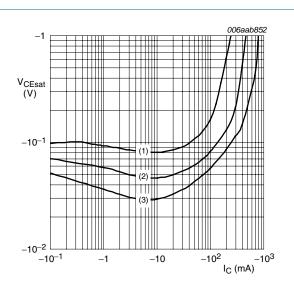
$$I_{\rm C}/I_{\rm B} = 10$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values

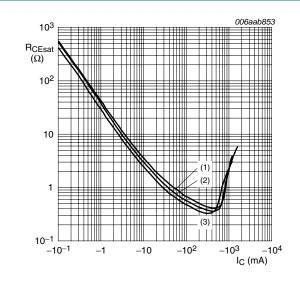


(1) 
$$I_C/I_B = 50$$

(2) 
$$I_C/I_B = 20$$

(3)  $I_C/I_B = 10$ 

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



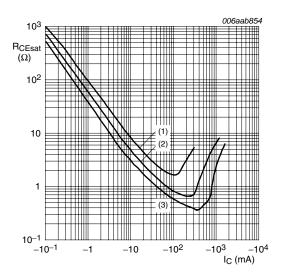
 $I_{\rm C}/I_{\rm B} = 10$ 

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

(1) 
$$I_C/I_B = 50$$

(2)  $I_C/I_B = 20$ 

(3)  $I_C/I_B = 10$ 

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values

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### 8. Test information

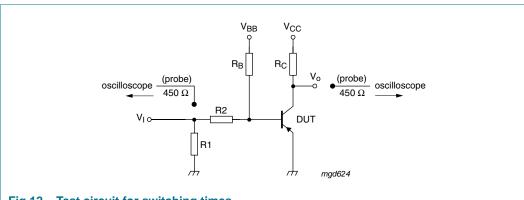
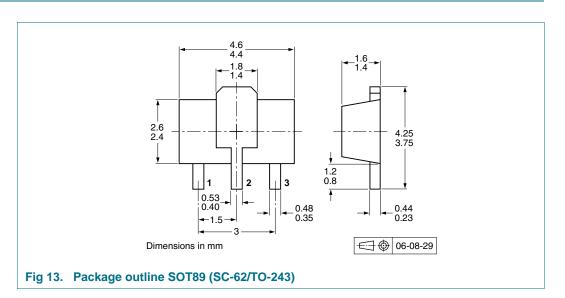


Fig 12. Test circuit for switching times

# 9. Package outline



# 10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity	
				1000	4000
PBHV9115X	SOT89	8 mm pitch, 12 mm tape and reel; T1	[2]	-115	-135
		8 mm pitch, 12 mm tape and reel; T3	[3]	-120	-

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T3: 90° taping

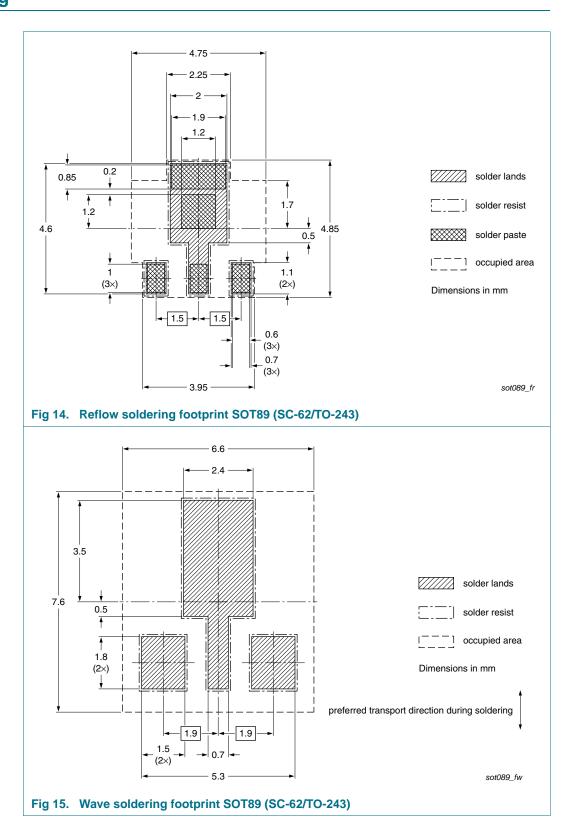
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# 11. Soldering



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# 12. Revision history

### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9115X_1	20100310	Product data sheet	-	-

### 150 V, 1 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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